

Thomas Schpers

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

200
papers

3,853
citations

32
h-index

52
g-index

223
ext. papers

4,199
ext. citations

4
avg, IF

4.97
L-index

#	Paper	IF	Citations
200	Investigation of Peculiarities of Coherent Magnetotransport of InN Nanowires Using Scanning Gate Microscopy. <i>Journal of Experimental and Theoretical Physics</i> , 2022 , 134, 95-102	1	0
199	Fully in situ Nb/InAs-nanowire Josephson junctions by selective-area growth and shadow evaporation. <i>Nanoscale Advances</i> , 2021 , 3, 1413-1421	5.1	3
198	Flux periodic oscillations and phase-coherent transport in GeTe nanowire-based devices. <i>Nature Communications</i> , 2021 , 12, 754	17.4	1
197	Proximity-Effect-Induced Superconductivity in Nb/Sb ₂ Te ₃ -Nanoribbon/Nb Junctions. <i>Annalen Der Physik</i> , 2020 , 532, 2000273	2.6	4
196	Phase coherent transport and spin-orbit interaction in GaAs/InSb core/shell nanowires. <i>Semiconductor Science and Technology</i> , 2020 , 35, 085003	1.8	1
195	Phase-coherent loops in selectively-grown topological insulator nanoribbons. <i>Nanotechnology</i> , 2020 , 31, 325001	3.4	4
194	Quantum Transport in Topological Surface States of Selectively Grown Bi ₂ Te ₃ Nanoribbons. <i>Advanced Electronic Materials</i> , 2020 , 6, 2000205	6.4	6
193	Exfoliated hexagonal BN as gate dielectric for InSb nanowire quantum dots with improved gate hysteresis and charge noise. <i>Applied Physics Letters</i> , 2020 , 116, 253101	3.4	2
192	Hard-Gap Spectroscopy in a Self-Defined Mesoscopic InAs/Al Nanowire Josephson Junction. <i>Physical Review Applied</i> , 2020 , 14,	4.3	2
191	Exploiting topological matter for Majorana physics and devices. <i>Solid-State Electronics</i> , 2019 , 155, 99-104	1.7	4
190	Signatures of induced superconductivity in AlO _x -capped topological heterostructures. <i>Solid-State Electronics</i> , 2019 , 155, 111-116	1.7	4
189	Selective area growth and stencil lithography for in situ fabricated quantum devices. <i>Nature Nanotechnology</i> , 2019 , 14, 825-831	28.7	33
188	Dresselhaus spin-orbit coupling in [111]-oriented semiconductor nanowires. <i>Physical Review B</i> , 2019 , 99,	3.3	5
187	Visualization and investigation of the non-thermalized electrons in an InAs nanowire by scanning gate microscopy. <i>Journal of Physics Condensed Matter</i> , 2019 , 31, 415302	1.8	1
186	Phase-coherent transport in selectively grown topological insulator nanodots. <i>Nanotechnology</i> , 2019 , 30, 055201	3.4	2
185	Quantum interferometer based on GaAs/InAs core/shell nanowires connected to superconducting contacts. <i>Semiconductor Science and Technology</i> , 2018 , 33, 064001	1.8	4
184	Phase-coherent transport in topological insulator nanocolumns and nanoribbons 2018 ,		1

183	Magnetotransport signatures of three-dimensional topological insulator nanostructures. <i>Physical Review B</i> , 2018 , 97,	3.3	10
182	Magnetoresistance oscillations in MBE-grown Sb ₂ Te ₃ thin films. <i>Applied Physics Letters</i> , 2017 , 110, 092104	3.4	7
181	Stencil lithography of superconducting contacts on MBE-grown topological insulator thin films. <i>Journal of Crystal Growth</i> , 2017 , 477, 183-187	1.6	9
180	Signatures of interaction-induced helical gaps in nanowire quantum point contacts. <i>Nature Physics</i> , 2017 , 13, 563-567	16.2	57
179	Electron Interference in Hall Effect Measurements on GaAs/InAs Core/Shell Nanowires. <i>Nano Letters</i> , 2017 , 17, 128-135	11.5	10
178	MBE growth of Al/InAs and Nb/InAs superconducting hybrid nanowire structures. <i>Nanoscale</i> , 2017 , 9, 16735-16741	7.7	17
177	Electrical properties of lightly Ga-doped ZnO nanowires. <i>Semiconductor Science and Technology</i> , 2017 , 32, 125010	1.8	6
176	Nano-Angle Resolved Photoemission Spectroscopy on Topological insulator Sb ₂ Te ₃ nanowires responsible of quantum transport. <i>Journal of Physics: Conference Series</i> , 2017 , 864, 012041	0.3	3
175	Anisotropic phase coherence in GaAs/InAs core/shell nanowires. <i>Nanotechnology</i> , 2017 , 28, 445202	3.4	2
174	Magnetoconductance correction in zinc-blende semiconductor nanowires with spin-orbit coupling. <i>Physical Review B</i> , 2017 , 96,	3.3	7
173	Strain relaxation and ambipolar electrical transport in GaAs/InSb core-shell nanowires. <i>Nanoscale</i> , 2017 , 9, 18392-18401	7.7	7
172	Stability of charged density waves in InAs nanowires in an external magnetic field. <i>Journal of Physics Condensed Matter</i> , 2017 , 29, 475601	1.8	2
171	Experimental determination of Rashba and Dresselhaus parameters and g*-factor anisotropy via Shubnikov-de Haas oscillations. <i>New Journal of Physics</i> , 2017 , 19, 103012	2.9	8
170	Impact of Tunnel-Barrier Strength on Magnetoresistance in Carbon Nanotubes. <i>Physical Review Applied</i> , 2016 , 5,	4.3	5
169	Weak (anti)localization in tubular semiconductor nanowires with spin-orbit coupling. <i>Physical Review B</i> , 2016 , 93,	3.3	21
168	Adiabatic Edge Channel Transport in a Nanowire Quantum Point Contact Register. <i>Nano Letters</i> , 2016 , 16, 4569-75	11.5	23
167	Growth, characterization, and transport properties of ternary (Bi Sb)Te topological insulator layers. <i>Journal of Physics Condensed Matter</i> , 2016 , 28, 495501	1.8	30
166	Topological insulator Sb ₂ Te ₃ /Bi ₂ Te ₃ heterostructures: structural properties 2016 , 1084-1085		

165	Angle-dependent magnetotransport in GaAs/InAs core/shell nanowires. <i>Scientific Reports</i> , 2016 , 6, 24573-9	4.9	9
164	Selective area growth of Bi ₂ Te ₃ and Sb ₂ Te ₃ topological insulator thin films. <i>Journal of Crystal Growth</i> , 2016 , 443, 38-42	1.6	19
163	P-N Junctions in Ultrathin Topological Insulator Sb ₂ Te ₃ /Bi ₂ Te ₃ Heterostructures Grown by Molecular Beam Epitaxy. <i>Crystal Growth and Design</i> , 2016 , 16, 2057-2061	3.5	29
162	Crystal Phase Transformation in Self-Assembled InAs Nanowire Junctions on Patterned Si Substrates. <i>Nano Letters</i> , 2016 , 16, 1933-41	11.5	24
161	Schmalbuch et al. Reply. <i>Physical Review Letters</i> , 2016 , 117, 139702	7.4	
160	Electronic Properties of Complex Self-Assembled InAs Nanowire Networks. <i>Advanced Electronic Materials</i> , 2016 , 2, 1500460	6.4	9
159	Confinement and inhomogeneous broadening effects in the quantum oscillatory magnetization of quantum dot ensembles. <i>Journal of Physics Condensed Matter</i> , 2016 , 28, 045301	1.8	2
158	Quantum Transport and Nano Angle-resolved Photoemission Spectroscopy on the Topological Surface States of Single Sb ₂ Te ₃ Nanowires. <i>Scientific Reports</i> , 2016 , 6, 29493	4.9	35
157	Ballistic Transport and Exchange Interaction in InAs Nanowire Quantum Point Contacts. <i>Nano Letters</i> , 2016 , 16, 3116-23	11.5	37
156	Micro-pixel light emitting diodes: Impact of the chip process on microscopic electro- and photoluminescence. <i>Applied Physics Letters</i> , 2015 , 106, 151108	3.4	11
155	Resolving ambiguities in nanowire field-effect transistor characterization. <i>Nanoscale</i> , 2015 , 7, 18188-97	7.7	25
154	Correlations of the mutual positions of the nodes of charge density waves in side-by-side placed InAs wires measured with scanning gate microscopy. <i>JETP Letters</i> , 2015 , 101, 628-632	1.2	4
153	Micromechanical measurement of beating patterns in the quantum oscillatory chemical potential of InGaAs quantum wells due to spin-orbit coupling. <i>Applied Physics Letters</i> , 2015 , 107, 092101	3.4	2
152	Realization of a vertical topological p-n junction in epitaxial Sb ₂ Te ₃ /Bi ₂ Te ₃ heterostructures. <i>Nature Communications</i> , 2015 , 6, 8816	17.4	70
151	Simultaneous integration of different nanowires on single textured Si (100) substrates. <i>Nano Letters</i> , 2015 , 15, 1979-86	11.5	7
150	Amphoteric nature of Sn in CdS nanowires. <i>Nano Letters</i> , 2014 , 14, 518-23	11.5	27
149	Giant magnetoconductance oscillations in hybrid superconductor-semiconductor core/shell nanowire devices. <i>Nano Letters</i> , 2014 , 14, 6269-74	11.5	15
148	Crystal Phase Selective Growth in GaAs/InAs Core/Shell Nanowires. <i>Crystal Growth and Design</i> , 2014 , 14, 1167-1174	3.5	23

147	Crossover from Josephson effect to single interface Andreev reflection in asymmetric superconductor/nanowire junctions. <i>Nano Letters</i> , 2014 , 14, 4977-81	11.5	19
146	Investigations of local electronic transport in InAs nanowires by scanning gate microscopy at liquid helium temperatures. <i>JETP Letters</i> , 2014 , 100, 32-38	1.2	6
145	Phase coherent transport in hollow InAs nanowires. <i>Applied Physics Letters</i> , 2014 , 105, 113111	3.4	6
144	Flux periodic magnetoconductance oscillations in GaAs/InAs core/shell nanowires. <i>Physical Review B</i> , 2014 , 89,	3.3	40
143	Quantum dots in InAs nanowires induced by surface potential fluctuations. <i>Nanotechnology</i> , 2014 , 25, 135203	3.4	7
142	The electronic transport of top subband and disordered sea in an InAs nanowire in the presence of a mobile gate. <i>Journal of Physics Condensed Matter</i> , 2014 , 26, 165304	1.8	6
141	Self-catalyzed VLS grown InAs nanowires with twinning superlattices. <i>Nanotechnology</i> , 2013 , 24, 335601	3.4	52
140	Frequency anomaly in the Rashba-effect induced magnetization oscillations of a high-mobility two-dimensional electron system. <i>Physical Review B</i> , 2013 , 87,	3.3	9
139	Controlled wurtzite inclusions in self-catalyzed zinc blende III-V semiconductor nanowires. <i>Journal of Crystal Growth</i> , 2013 , 378, 506-510	1.6	28
138	Nanoimprint and selective-area MOVPE for growth of GaAs/InAs core/shell nanowires. <i>Nanotechnology</i> , 2013 , 24, 085603	3.4	42
137	Distortions of the coulomb blockade conductance line in scanning gate measurements of InAs nanowire based quantum dots. <i>Journal of Experimental and Theoretical Physics</i> , 2013 , 116, 138-144	1	6
136	Gate-induced transition between metal-type and thermally activated transport in self-catalyzed MBE-grown InAs nanowires. <i>Nanotechnology</i> , 2013 , 24, 325201	3.4	4
135	Realization of nanoscaled tubular conductors by means of GaAs/InAs core/shell nanowires. <i>Nanotechnology</i> , 2013 , 24, 035203	3.4	35
134	Electrical spin injection into InN semiconductor nanowires. <i>Nano Letters</i> , 2012 , 12, 4437-43	11.5	31
133	Direct observation of standing electron waves in diffusively conducting InAs nanowire. <i>JETP Letters</i> , 2012 , 96, 109-112	1.2	5
132	Hall effect measurements on InAs nanowires. <i>Applied Physics Letters</i> , 2012 , 101, 152106	3.4	81
131	Negative differential conductance in InAs wire based double quantum dot induced by a charged AFM tip. <i>Journal of Experimental and Theoretical Physics</i> , 2012 , 115, 1062-1067	1	4
130	Molecular beam epitaxy growth of GaAs/InAs core-shell nanowires and fabrication of InAs nanotubes. <i>Nano Letters</i> , 2012 , 12, 5559-64	11.5	58

129	Comparison of InAs nanowire conductivity: influence of growth method and structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 230-234		7
128	Electronic transport with dielectric confinement in degenerate InN nanowires. <i>Nano Letters</i> , 2012 , 12, 2768-72	11.5	19
127	Scanning tunneling microscopy with InAs nanowire tips. <i>Applied Physics Letters</i> , 2012 , 101, 243101	3.4	4
126	Monitoring structural influences on quantum transport in InAs nanowires. <i>Applied Physics Letters</i> , 2012 , 101, 062104	3.4	5
125	Supercurrent in Nb/InAs-nanowire/Nb Josephson junctions. <i>Journal of Applied Physics</i> , 2012 , 112, 034316.5	16.5	29
124	Phase coherent transport in InSb nanowires. <i>Applied Physics Letters</i> , 2012 , 101, 082103	3.4	14
123	Preparation of Ohmic contacts to GaAs/AlGaAs-core/shell-nanowires. <i>Applied Physics Letters</i> , 2012 , 100, 042103	3.4	12
122	Effect of Si-doping on InAs nanowire transport and morphology. <i>Journal of Applied Physics</i> , 2011 , 110, 053709	2.5	55
121	Investigation of the surface properties of gold nanowire arrays. <i>Applied Surface Science</i> , 2011 , 258, 147-159	159	6
120	Electronic phase coherence in InAs nanowires. <i>Nano Letters</i> , 2011 , 11, 3550-6	11.5	63
119	Spin precession and modulation in ballistic cylindrical nanowires due to the Rashba effect. <i>Physical Review B</i> , 2011 , 83,	3.3	40
118	Low-temperature conductance of the weak junction in InAs nanowire in the field of AFM scanning gate. <i>JETP Letters</i> , 2011 , 93, 10-14	1.2	10
117	New method of creation of a rearrangeable local Coulomb potential profile and its application for investigations of local conductivity of InAs nanowires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2011 , 44, 690-695	3	5
116	Field effect transistor based on single crystalline InSb nanowire. <i>Journal of Materials Chemistry</i> , 2011 , 21, 2459		47
115	Manipulating InAs nanowires with submicrometer precision. <i>Review of Scientific Instruments</i> , 2011 , 82, 113705	1.7	28
114	Optical and electrical properties of gold nanowires synthesized by electrochemical deposition. <i>Journal of Applied Physics</i> , 2011 , 110, 094301	2.5	15
113	Two-dimensional optical control of electron spin orientation by linearly polarized light in InGaAs. <i>Physical Review Letters</i> , 2010 , 105, 246603	7.4	9
112	Universal conductance fluctuations and localization effects in InN nanowires connected in parallel. <i>Journal of Applied Physics</i> , 2010 , 108, 113704	2.5	16

111	Josephson supercurrent in Nb/InN-nanowire/Nb junctions. <i>Applied Physics Letters</i> , 2010 , 96, 132504	3.4	26
110	LaLuO ₃ as a high-k gate dielectric for InAs nanowire structures. <i>Semiconductor Science and Technology</i> , 2010 , 25, 085001	1.8	5
109	Spin-orbit coupling and phase coherence in InAs nanowires. <i>Physical Review B</i> , 2010 , 82,	3.3	74
108	Improved gate-control in InAs nanowire structures by the use of GdScO ₃ as a gate dielectric. <i>Applied Physics A: Materials Science and Processing</i> , 2010 , 100, 305-308	2.6	1
107	Nanowires: Technology, Physics and Perspectives 2010 , 171-181		
106	Strain-enhanced electron mobility anisotropy in In _x Ga _{1-x} As/InP two-dimensional electron gases. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010 , 42, 1130-1133	3	3
105	Quantum transport in narrow-gap semiconductor nanocolumns. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 386-389		5
104	Spin-orbit coupling and phase-coherent transport in InN nanowires. <i>Physical Review B</i> , 2009 , 80,	3.3	24
103	Origin and limiting mechanism of induced nonequilibrium currents in gated two-dimensional electron systems. <i>Physical Review B</i> , 2009 , 80,	3.3	8
102	Phase-coherence and symmetry in four-terminal magnetotransport measurements on InN nanowires. <i>Applied Physics Letters</i> , 2009 , 94, 252107	3.4	14
101	Measurement of effective electron mass in biaxial tensile strained silicon on insulator. <i>Applied Physics Letters</i> , 2009 , 95, 182101	3.4	24
100	Electrical transport properties of single undoped and n-type doped InN nanowires. <i>Nanotechnology</i> , 2009 , 20, 405206	3.4	42
99	Spin-orbit coupling in Ga _x In _{1-x} As/InP two-dimensional electron gases and quantum wire structures. <i>Semiconductor Science and Technology</i> , 2009 , 24, 064001	1.8	11
98	Study on growth and electrical performance of double-heterostructure AlGa _N /Ga _N /AlGa _N field-effect-transistors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S1003-S1006		5
97	Influence of barrier thickness on AlInN/AlN/GaN heterostructures and device properties. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S1041-S1044		10
96	Influence of growth temperature on the selective area MOVPE of InAs nanowires on GaAs (1 1 1) B using N ₂ carrier gas. <i>Journal of Crystal Growth</i> , 2009 , 311, 3813-3816	1.6	32
95	Influence of growth temperature on GaN:Cr incorporation and structural properties in MOVPE. <i>Journal of Crystal Growth</i> , 2009 , 312, 1-9	1.6	8
94	In _x Ga _{1-x} As/InP selective area metal-organic vapor phase epitaxy for non-magnetic semiconductor spintronics. <i>Journal of Crystal Growth</i> , 2008 , 310, 4821-4825	1.6	1

93	Flux quantization effects in InN nanowires. <i>Nano Letters</i> , 2008 , 8, 2834-8	11.5	66
92	Phase-coherent transport in InN nanowires of various sizes. <i>Physical Review B</i> , 2008 , 77,	3.3	25
91	Temperature dependence of the phase-coherence length in InN nanowires. <i>Applied Physics Letters</i> , 2008 , 92, 132101	3.4	28
90	Spin-splitting analysis of a two-dimensional electron gas in almost strain-free In _{0.89} Ga _{0.11} Sb/In _{0.88} Al _{0.12} Sb by magnetoresistance measurements. <i>Physical Review B</i> , 2008 , 77,	3.3	23
89	Weak antilocalization in high mobility Ga _x In _{1-x} As/InP two-dimensional electron gases with strong spin-orbit coupling. <i>Physical Review B</i> , 2007 , 76,	3.3	36
88	The growth of Cr-doped GaN by MOVPE towards spintronic applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 72-77	1.6	3
87	Rashba effect in Ga _x In _{1-x} As/InP quantum wire structures. <i>Applied Physics A: Materials Science and Processing</i> , 2007 , 87, 577-584	2.6	10
86	Suppression of weak antilocalization in an Al _x Ga _{1-x} N/GaN two-dimensional electron gas by an in-plane magnetic field. <i>Physical Review B</i> , 2007 , 75,	3.3	6
85	Andreev reflection and strongly enhanced magnetoresistance oscillations in Ga _x In _{1-x} As/InP heterostructures with superconducting contacts. <i>Physical Review B</i> , 2007 , 76,	3.3	22
84	Zeeman splitting in ballistic GaInAs/InP split-gate quantum point contacts. <i>Applied Physics Letters</i> , 2007 , 90, 122107	3.4	14
83	Enhanced spin-orbit scattering length in narrow Al _x Ga _{1-x} N/GaN wires. <i>Physical Review B</i> , 2007 , 76,	3.3	33
82	Weak antilocalization in gate-controlled Al _x Ga _{1-x} N/GaN two-dimensional electron gases. <i>Physical Review B</i> , 2006 , 73,	3.3	47
81	Rashba effect in InGaAs/InP parallel quantum wires. <i>Applied Physics Letters</i> , 2006 , 88, 032102	3.4	29
80	Suppression of weak antilocalization in Ga _x In _{1-x} As/InP narrow quantum wires. <i>Physical Review B</i> , 2006 , 74,	3.3	59
79	Weak antilocalization in a polarization-doped Al _x Ga _{1-x} N/GaN heterostructure with single subband occupation. <i>Applied Physics Letters</i> , 2006 , 88, 022111	3.4	49
78	Spin-orbit coupling in gated AlGa _N /Ga _N 2-dimensional electron gases. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 4247-4250		2
77	Weak antilocalization measurements on a 2-dimensional electron gas in an InGaSb/InAlSb heterostructure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 4227-4230		8
76	Effect of confinement on the weak antilocalization in InGaAs/InP quasi-1D structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006 , 32, 333-336	3	1

75	Magnetosubbands of semiconductor quantum wires with Rashba spin-orbit coupling. <i>Physical Review B</i> , 2005 , 71,	3.3	47
74	Localized electrochemical oxidation of thin Nb Films in microscopic and nanoscopic dimensions. <i>Surface Science</i> , 2005 , 597, 173-180	1.8	10
73	Principles of electrochemical nanotechnology and their application for materials and systems. <i>Electrochimica Acta</i> , 2005 , 51, 775-786	6.7	13
72	Epitaxial growth of Fe on GaN(0001): structural and magnetic properties. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 754-757	1.6	11
71	Longitudinal photocurrent spectroscopy of a single GaAs/AlGaAs v-groove quantum wire. <i>Nanotechnology</i> , 2005 , 16, 307-11	3.4	3
70	Shot noise of large charge quanta in superconductor/semiconductor/superconductor junctions. <i>Physical Review B</i> , 2005 , 71,	3.3	5
69	Weak Antilocalization in Polarization-Doped Al _x Ga _{1-x} N/GaN Heterostructures. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 892, 370		
68	Effect of Rashba spin-orbit coupling on magnetotransport in InGaAs/InP quantum wire structures. <i>Physical Review B</i> , 2004 , 69,	3.3	69
67	Andreev reflection and enhanced subgap conductance in NbN/Au/InGaAs-InP junctions. <i>Journal of Applied Physics</i> , 2004 , 96, 3366-3370	2.5	14
66	Magnetic and structural properties of GaN thin layers implanted with Mn, Cr, or V ions. <i>Journal of Applied Physics</i> , 2004 , 96, 5663-5667	2.5	18
65	Rashba spin-orbit coupling in InGaAs/InP quantum wires. <i>Materials Research Society Symposia Proceedings</i> , 2004 , 825, G5.7.1		
64	Rashba effect in gated InGaAs/InP quantum wire structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 21, 933-936	3	6
63	Carrier relaxation in GaAs v-groove quantum wires and the effects of localization. <i>Physical Review B</i> , 2004 , 70,	3.3	6
62	Supercurrent control in a multi-terminal Nb-InGaAs/InP junction with Nb injector electrodes. <i>Superconductor Science and Technology</i> , 2003 , 16, 714-719	3.1	1
61	Rashba effect in strained InGaAs/InP quantum wire structures. <i>Science and Technology of Advanced Materials</i> , 2003 , 4, 19-25	7.1	12
60	Current-injection in a ballistic multiterminal superconductor/two-dimensional electron gas Josephson junction. <i>Physical Review B</i> , 2003 , 67,	3.3	17
59	Coherent "metallic" resistance and medium localization in a disordered one-dimensional insulator. <i>Physical Review Letters</i> , 2003 , 91, 136803	7.4	13
58	Control of interference effects in a two-dimensional-electron-gas/superconductor junction by the Josephson effect. <i>Physical Review B</i> , 2003 , 67,	3.3	1

57	Coherent resistance of a disordered one-dimensional wire: Expressions for all moments and evidence for non-Gaussian distribution. <i>Physical Review B</i> , 2003 , 67,	3.3	5
56	Optical measurements of carrier relaxation and transport in single GaAs v-groove quantum wire structures. <i>Physica B: Condensed Matter</i> , 2002 , 314, 413-416	2.8	5
55	Dephasing of coherent one-dimensional transport in a disordered wire. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002 , 12, 703-707	3	
54	2D/1D crossover from quantum well to quantum wire behaviour in GaAs v-groove structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002 , 13, 174-177	3	2
53	Model for ballistic spin-transport in ferromagnet/two-dimensional electron gas/ferromagnet structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002 , 13, 564-567	3	4
52	Investigation of Ferromagnetic Microstructures by Local Hall Effect and Magnetic Force Microscopy. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, 2497-2500	1.4	8
51	Carrier transport in multi-terminal superconductor/two-dimensional electron gas Josephson junctions. <i>Physica C: Superconductivity and Its Applications</i> , 2001 , 352, 144-148	1.3	1
50	Control of Aharonov-Bohm oscillations in a AlGaAs/GaAs ring by asymmetric and symmetric gate biasing. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2001 , 9, 635-641	3	12
49	Superconductor/Semiconductor Junctions. <i>Springer Tracts in Modern Physics</i> , 2001 ,	0.1	50
48	Enhancement of spin injection from ferromagnetic metal into a two-dimensional electron gas using a tunnel barrier. <i>Physical Review B</i> , 2001 , 64,	3.3	45
47	Interference ferromagnet/semiconductor/ferromagnet spin field-effect transistor. <i>Physical Review B</i> , 2001 , 64,	3.3	44
46	Scanning Near-Field Optical Spectroscopy of Buried Semiconductor Heterostructures. <i>Springer Proceedings in Physics</i> , 2001 , 703-704	0.2	3
45	On the choice of precursors for the MOVPE-growth of high-quality Al _{0.30} Ga _{0.70} As/GaAs v-groove quantum wires with large subband spacing. <i>Journal of Crystal Growth</i> , 2000 , 221, 91-97	1.6	8
44	Electron transport in modulation-doped GaAs v-groove quantum wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 7, 760-765	3	8
43	Fermi-edge singularities in the photoluminescence and magneto-optical spectra of modulation-doped v-groove quantum wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 6, 530-533	3	2
42	Fermi-edge singularities in the photoluminescence spectrum of modulation-doped GaAs v-groove quantum wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 7, 517-520	3	2
41	Preparation of transparent Nb/two-dimensional electron gas contacts by using electron cyclotron resonance plasma cleaning. <i>Journal of Applied Physics</i> , 2000 , 88, 4440	2.5	4
40	Splitting of the subgap resistance peak in superconductor/two-dimensional electron gas contacts at high magnetic fields. <i>Physical Review B</i> , 2000 , 61, 12463-12466	3.3	17

39	Adjustment of the critical current in a Nb _{1-x} Ga _{1-x} As/InP Josephson contact by light exposure. <i>Applied Physics Letters</i> , 1999 , 75, 391-393	3.4	9
38	Local suppression of Josephson currents in niobium/two-dimensional electron gas/niobium structures by an injection current. <i>Physical Review B</i> , 1999 , 59, 11197-11200	3.3	19
37	Suppression of the surface-inversion layer of p-type InAs. <i>Journal of Applied Physics</i> , 1999 , 85, 8242-8246	2.5	1
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31	Electrical and structural studies of AlGaAs/GaAs wires grown on patterned substrates. <i>Applied Surface Science</i> , 1998 , 123-124, 687-693	6.7	8
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10	Magnetotransport and photoluminescence of two-dimensional hole gases in $\text{Si}/\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ heterostructures. <i>Physical Review B</i> , 1994 , 50, 18113-18123	3.3	12
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